

AMENDMENTS TO THE CLAIMS

The following listing of claims will replace all prior versions and listings of claims in the application.

LISTING OF CLAIMS

1. (Currently Amended) A method for manufacturing a semiconductor device ~~including electrodes, a plurality of protrusions which protrude higher than the electrodes and which are made of a resin in a predetermined pattern, and conductive layers which are electrically connected to the electrodes and which cover top surfaces of the protrusions, the method comprising the steps of:~~

forming a plurality of electrodes on a semiconductor element;

applying a layer of the a resin to the semiconductor device element in a region of the element that does not include except for the electrodes, the layer of resin being applied such that a height of the layer is greater than a height of the electrodes;

forming a conductive layer over the plurality of electrodes and the layer of resin;

patterning the conductive layer[[s]] on the electrodes and the layer of the resin in accordance with a predetermined pattern of the protrusions; and

removing portions of the layer of the resin located between the by using the patterned conductive layer[[s]] by the use of the patterned conductive layers as a masks, mask so as that remaining portions of the layer of resin to form the a plurality of protrusions.

2. (Original) The method for manufacturing a semiconductor device according to Claim 1, wherein the layer of the resin is removed by plasma processing.

3. (Currently Amended) The method for manufacturing a semiconductor device according to Claim 1, wherein the conductive layer[[s]] is ~~are~~ formed by sputtering.

4. (Currently Amended) The method for manufacturing a semiconductor device according to Claim 1, wherein the conductive layer[[s]] is ~~are~~ formed by plating.

5. (Currently Amended) The method for manufacturing a semiconductor device according to claim 1, wherein the step of ~~patterning~~ forming the conductive layer[[s]] comprises ~~the sub-steps of:~~

forming a first conductive layer[[s]] that covering covers the electrodes before the layer of ~~the~~ resin is formed; and

forming a second conductive layer[[s]] after the layer of resin is applied, the second conductive layer ~~which are~~ being connected to the first conductive layer[[s]] and ~~which covering~~ a top surface of the layer of ~~the~~ resin.

6. (Currently Amended) The method for manufacturing a semiconductor device according to Claim 5, wherein the first conductive layer[[s]] is ~~are~~ formed by electroless nickel plating.

7. – 13. (Cancelled)